

Low Capacitance, Bidirectional Transient Voltage Suppressor

Descriptions

The ESD5B5VL is an ESD transient voltage suppression component which provides a very high level of protection for sensitive electronic components that may be subjected to electrostatic discharge (ESD). It is particularly well-suited for cellular phones, portable device, digital cameras, power supplies and many other portable applications because of its small package and low weight.

The ESD5B5VL is Bidirectional, Safely dissipate ESD strikes of Level 4, IEC61000-4-2, exceeding the maximum requirement. Using the MILSTD-883 (Method 3015) specification for Human Body Model (HBM) ESD, the device provides protection for contact discharges to greater than +/-16KV.

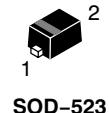
The ESD5B5VL is available in a SOD-523 package with peak reverse working voltage of 5 voltages.

Features

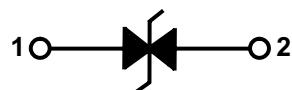
- Peak Reverse Working Voltage: 5V
- Peak power up to 100W @ 8 x 20 us Pulse
- Low leakage current
- Low Capacitance : 3PF
- High ESD protection Level: >+/-16KV per HBM
- IEC61000-4-2 Level 4 ESD Protection
- IEC61000-4-4 Level 4 EFT Protection

Applications

- Cell phone handsets and accessories
- Personal Digital Assistants (PDAs)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Digital Cameras
- MP3/MP4/PMP Players



Package Diagram



Pin Configuration



X = Date Code

B = Special Device Code

Marking Diagram and explain

Order Information

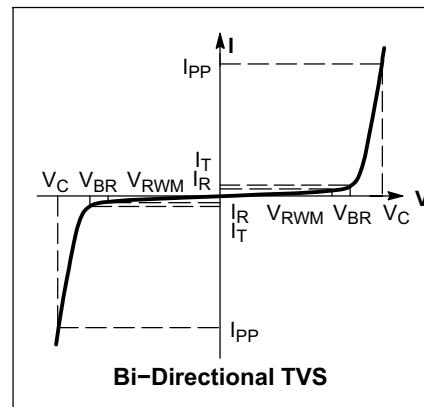
Device	Package	Shipping
ESD5B5VL-2/TR	SOD-523	3000/Tape&Reel

Maximum Ratings

Rating	Symbol	Value	Units
Peak pulse power (tp=8/20 us)	Ppk	100	W
Maximum peak pulse current (tp=8/20us)	Ipp	12	A
ESD Per IEC61000-4-2 (Air)	Vpp	+/-30	KV
ESD Per IEC61000-4-2 (Contact)		+/-30	
Maximum lead temperature for soldering during 10s	T _L	260	°C
Storage temperature range	T _{stg}	-55 to +150	°C
Operating temperature range	T _{op}	-55 to +150	°C

Electronics Parameter

Symbol	Parameter
V _{rwm}	Peak Reverse Working Voltage
I _r	Reverse Leakage Current @ V _{rwm}
V _b	Breakdown Voltage @ I _t
I _t	Test Current
I _{pp}	Maximum Reverse Peak Pulse Current
V _c	Clamping Voltage @ I _{pp}
P _{pk}	Peak Power Dissipation
C	Junction Capacitance
I _f	Forward Current
V _f	Forward Voltage @ I _f

**Electronics Characteristics**

Device	Marking	V _{rwm} (V)	I _r (uA) @V _{rwm}	V _b (V) @ I _t (Note1)	I _t (mA)	I _{pp} (A)	V _c (V) @ Max I _{pp}	P _{pk} (W) (8 x 20us) (Note2)	C (pF)	
		Max.	Max.	Min.	Typ.	Max.	Max.	Typ.	Typ.	Max.
ESD5B5VL-2/TR	XX	5.0	1	5.8	1	12	9.5	100	3	6

Note 1: V_b is measured with a pulse current I_t.

Note 2: Surge current waveform per Figure 1.

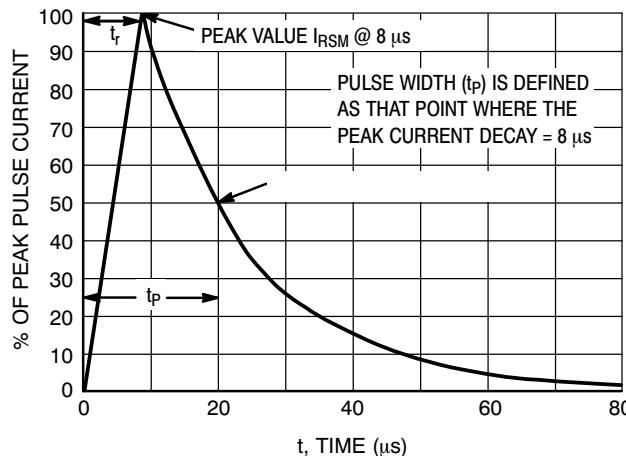


Figure1. 8x20us pulse waveform

Typical Performance Graph

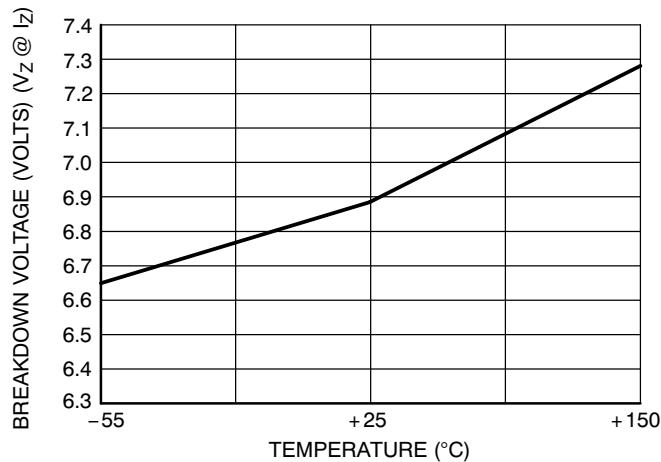


Figure2. Typical breakdown voltage vs temperature

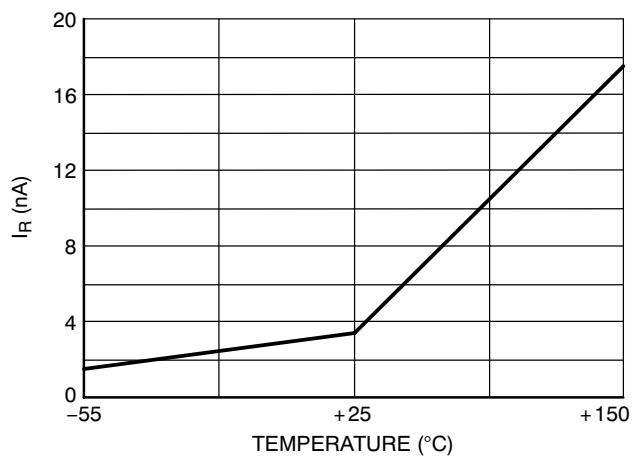
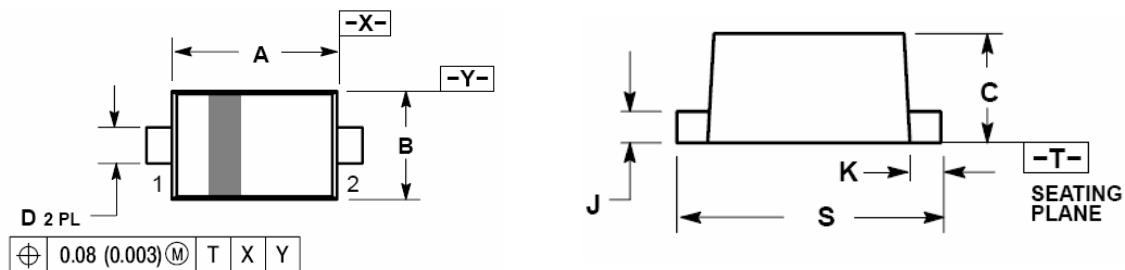


Figure3. Typical leakage current vs temperature

Package mechanical data



Dim	Millimeters				Inches			
	Min	Nom	Max	Min	Nom	Max	Min	Nom
A	1.10	1.20	1.30	0.043	0.047	0.051	A	1.10
B	0.70	0.80	0.90	0.028	0.032	0.035	B	0.70
C	0.50	0.60	0.70	0.020	0.024	0.028	C	0.50
D	0.25	0.30	0.35	0.010	0.012	0.014	D	0.25
J	0.07	0.14	0.20	0.0028	0.0055	0.0079	J	0.07
K	0.15	0.20	0.25	0.006	0.008	0.010	K	0.15
S	1.50	1.60	1.70	0.059	0.063	0.067	S	1.50